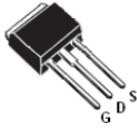

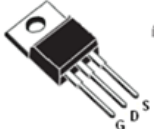

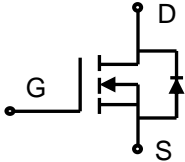



## Lonten N-channel 650V, 2A Power MOSFET

<p><b>Description</b> The Power MOSFET is fabricated using the advanced planer VDMOS technology. The resulting device has low conduction resistance, superior switching performance and high avalanche energy.</p> <p><b>Features</b></p> <ul style="list-style-type: none"> <li>◆ Low <math>R_{DS(on)}</math></li> <li>◆ Low gate charge (typ. <math>Q_g = 10.2</math> nC)</li> <li>◆ 100% UIS tested</li> <li>◆ RoHS compliant</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>◆ Power factor correction.</li> <li>◆ Switched mode power supplies.</li> <li>◆ LED driver.</li> </ul>	<p><b>Product Summary</b></p> <table> <tr> <td><math>V_{DSS}</math></td> <td>650V</td> </tr> <tr> <td><math>I_D</math></td> <td>2A</td> </tr> <tr> <td><math>R_{DS(on),max}</math></td> <td>5.2<math>\Omega</math></td> </tr> <tr> <td><math>Q_{g,typ}</math></td> <td>10.2 nC</td> </tr> </table> <div style="display: flex; justify-content: space-around; align-items: center;"> <div style="text-align: center;">  TO-251         </div> <div style="text-align: center;">  TO-252         </div> <div style="text-align: center;">  TO-220         </div> <div style="text-align: center;">  TO-220F         </div> </div> <div style="text-align: center; margin-top: 20px;">  N-Channel MOSFET         </div> <div style="text-align: right; margin-top: 10px;">  </div>	$V_{DSS}$	650V	$I_D$	2A	$R_{DS(on),max}$	5.2 $\Omega$	$Q_{g,typ}$	10.2 nC
$V_{DSS}$	650V								
$I_D$	2A								
$R_{DS(on),max}$	5.2 $\Omega$								
$Q_{g,typ}$	10.2 nC								

### Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	650	V
Continuous drain current ( $T_C = 25^\circ\text{C}$ ) ( $T_C = 100^\circ\text{C}$ )	$I_D$	2	A
		1.3	A
Pulsed drain current <sup>1)</sup>	$I_{DM}$	8	A
Gate-Source voltage	$V_{GSS}$	$\pm 30$	V
Avalanche energy, single pulse <sup>2)</sup>	$E_{AS}$	80	mJ
Peak diode recovery dv/dt <sup>3)</sup>	dv/dt	5	V/ns
Power Dissipation TO-220F ( $T_C = 25^\circ\text{C}$ ) Derate above 25°C	$P_D$	27	W
		0.22	W/°C
Power Dissipation TO-220\ TO-251\ TO-252 ( $T_C = 25^\circ\text{C}$ ) Derate above 25°C	$P_D$	35	W
		0.28	W/°C
Operating junction and storage temperature range	$T_J, T_{STG}$	-55 to +150	°C
Continuous diode forward current	$I_S$	2	A
Diode pulse current	$I_{S,pulse}$	8	A

### Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO-220F	TO-220\TO-251\TO-252	
Thermal resistance, Junction-to-case	$R_{\theta JC}$	4.63	3.57	°C/W
Thermal resistance, Junction-to-ambient	$R_{\theta JA}$	100	62	°C/W

**Package Marking and Ordering Information**

Device	Device Package	Marking	Units/Tube	Units/Real
LNC2N65	TO-220	LNC2N65	50	
LND2N65	TO-220F	LND2N65	50	
LNG2N65	TO-252	LNG2N65		3000
LNH2N65	TO-251	LNH2N65	80	

**Electrical Characteristics**  $T_c = 25^\circ\text{C}$  unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static characteristics</b>						
Drain-source breakdown voltage	$BV_{DSS}$	$V_{GS}=0\text{ V}, I_D=0.25\text{ mA}$	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.25\text{ mA}$	2	-	4	V
Drain cut-off current	$I_{DSS}$	$V_{DS}=650\text{ V}, V_{GS}=0\text{ V},$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	-	-	1 100	$\mu\text{A}$
Gate leakage current, Forward	$I_{GSSF}$	$V_{GS}=30\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Gate leakage current, Reverse	$I_{GSSR}$	$V_{GS}=-30\text{ V}, V_{DS}=0\text{ V}$	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=1\text{ A}$	-	4.2	5.2	$\Omega$
<b>Dynamic characteristics</b>						
Input capacitance	$C_{iss}$	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$	-	338	-	pF
Output capacitance	$C_{oss}$		-	36	-	
Reverse transfer capacitance	$C_{rss}$		-	3.4	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 325\text{ V}, I_D = 2\text{ A}$ $R_G = 10\ \Omega, V_{GS}=15\text{ V}$	-	17.2	-	ns
Rise time	$t_r$		-	35.6	-	
Turn-off delay time	$t_{d(off)}$		-	33.9	-	
Fall time	$t_f$		-	29	-	
<b>Gate charge characteristics</b>						
Gate to source charge	$Q_{gs}$	$V_{DD}=520\text{ V}, I_D=2\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	2.6	-	nC
Gate to drain charge	$Q_{gd}$		-	4.7	-	
Gate charge total	$Q_g$		-	10.2	-	
Gate plateau voltage	$V_{plateau}$		-	5	-	V
<b>Reverse diode characteristics</b>						
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=2\text{ A}$	-	-	1.5	V
Reverse recovery time	$t_{rr}$	$V_R=400\text{ V}, I_F=2\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	221.8	-	ns
Reverse recovery charge	$Q_{rr}$		-	0.75	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	7.4	-	A

**Notes:**

- Pulse width limited by maximum junction temperature.
- $L=10\text{mH}, I_{AS} = 4\text{A},$  Starting  $T_j= 25^\circ\text{C}.$
- $I_{SD} = 2\text{A}, di/dt \leq 100\text{A}/\mu\text{s}, V_{DD} \leq BV_{DS},$  Starting  $T_j= 25^\circ\text{C}.$

### Electrical Characteristics Diagrams

Figure 1. Typical Output Characteristics

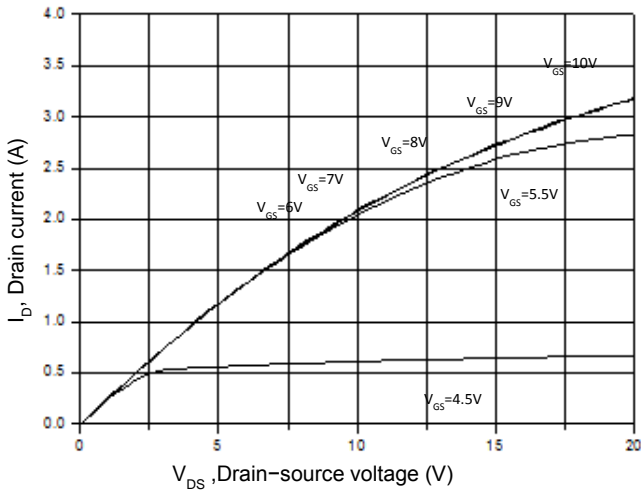


Figure 2. Transfer Characteristics

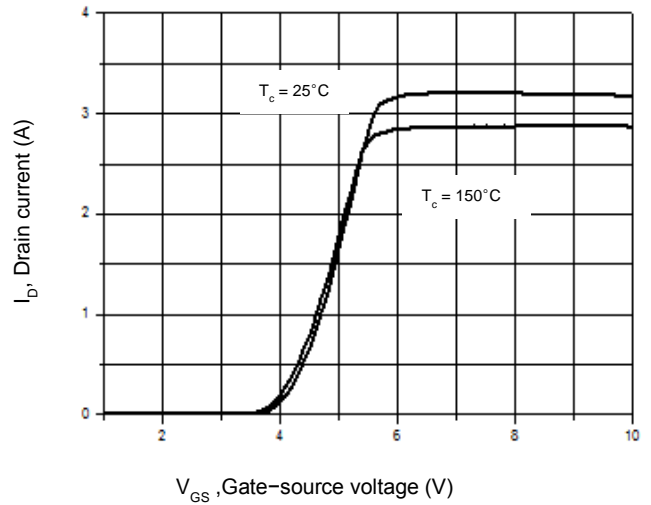


Figure 3. On-Resistance Variation vs. Drain Current

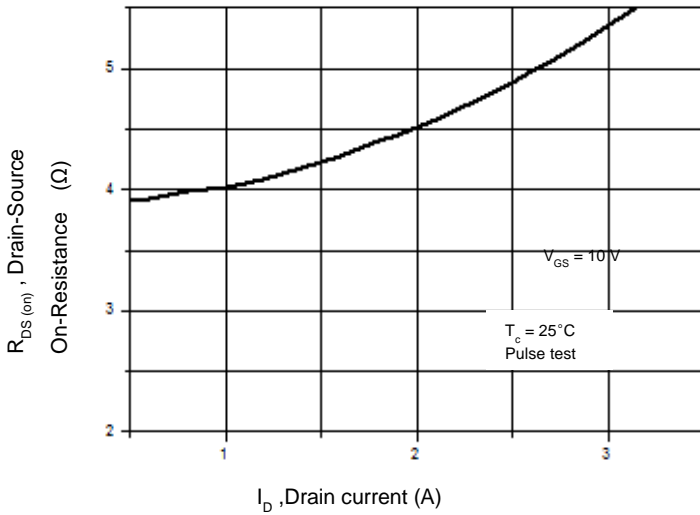


Figure 4. Threshold Voltage vs. Temperature

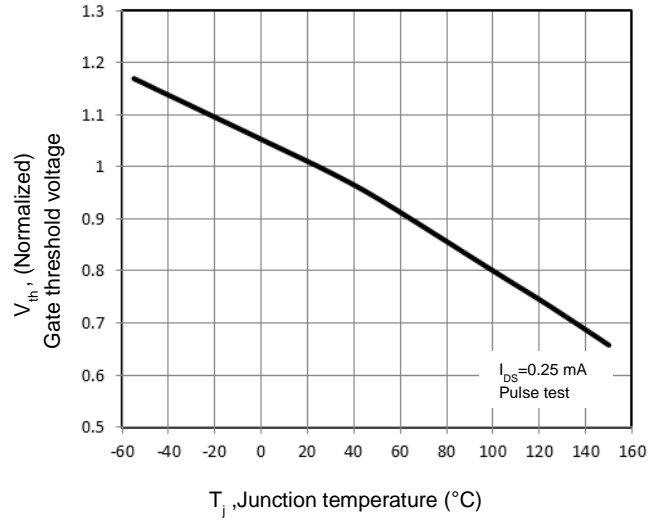


Figure 5. Breakdown Voltage vs. Temperature

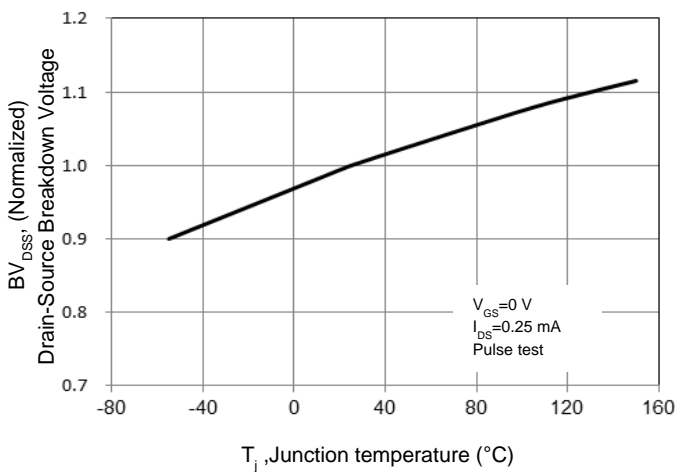


Figure 6. On-Resistance vs. Temperature

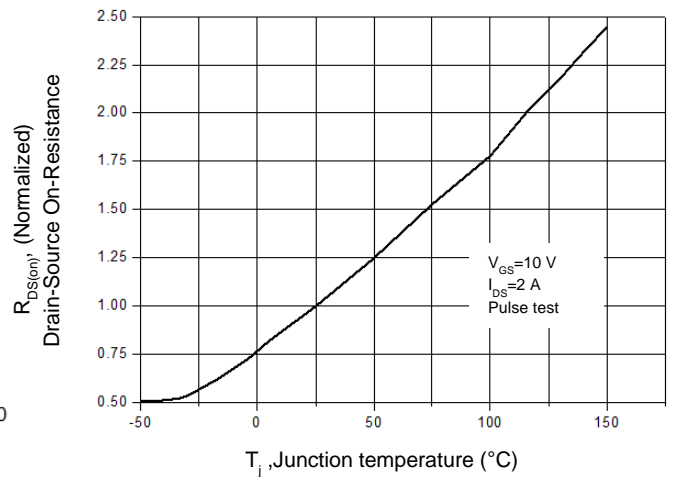


Figure 7. Capacitance Characteristics

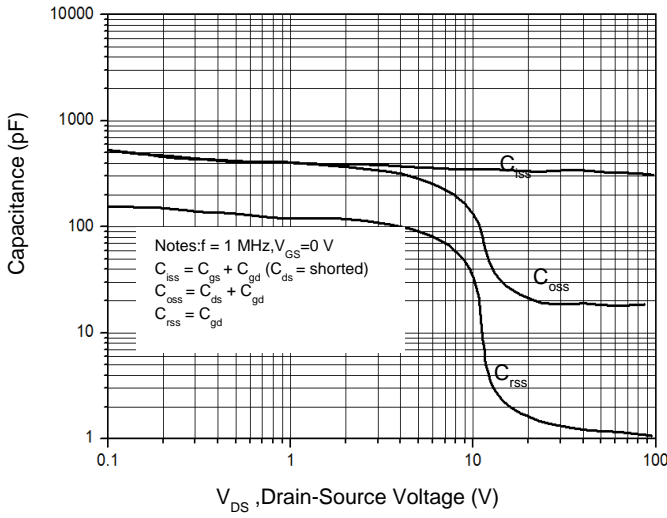


Figure 8. Gate Charge Characterist

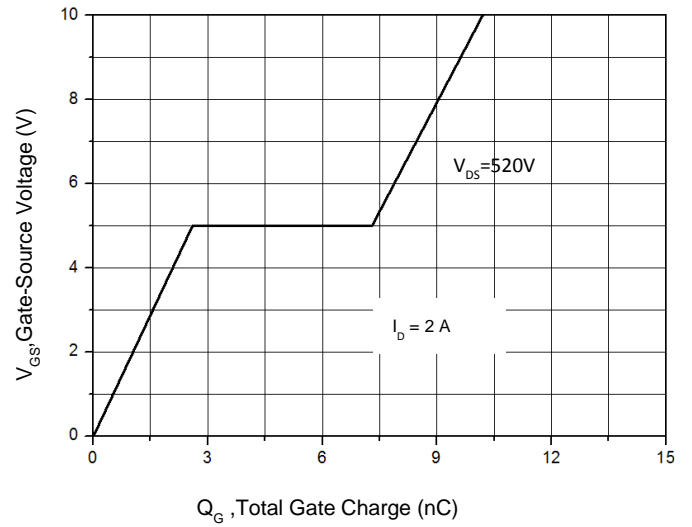


Figure 9. Maximum Safe Operating Area  
TO-220F

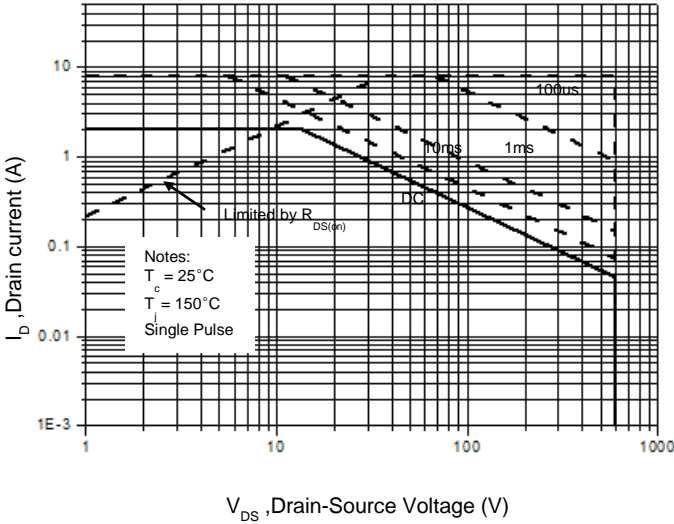


Figure 10. Maximum Safe Operating Area  
TO-220/ TO-251/TO-252

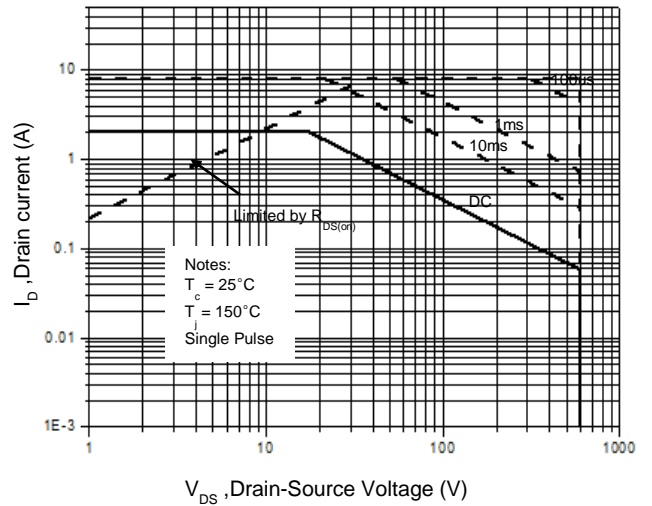


Figure 11. Power Dissipation vs. Temperature  
TO-220F

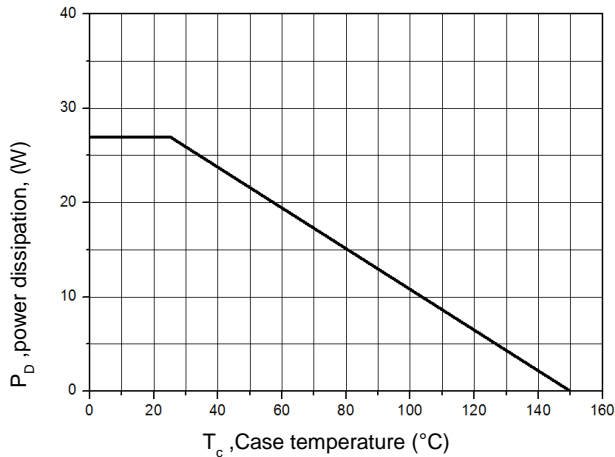


Figure 12. Power Dissipation vs. Temperature  
TO-220/ TO-251/TO-252

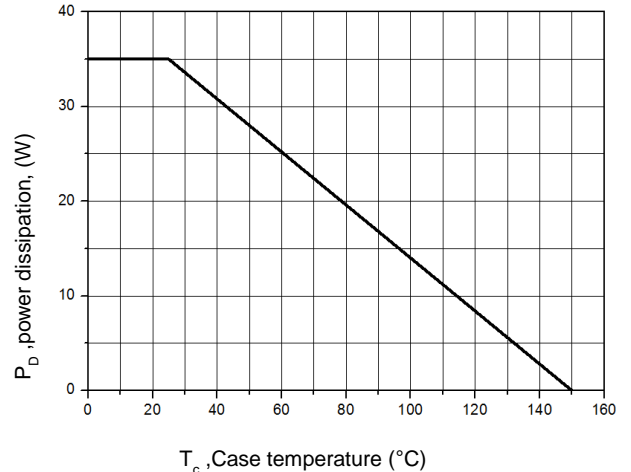


Figure 13. Continuous Drain Current vs. Temperature

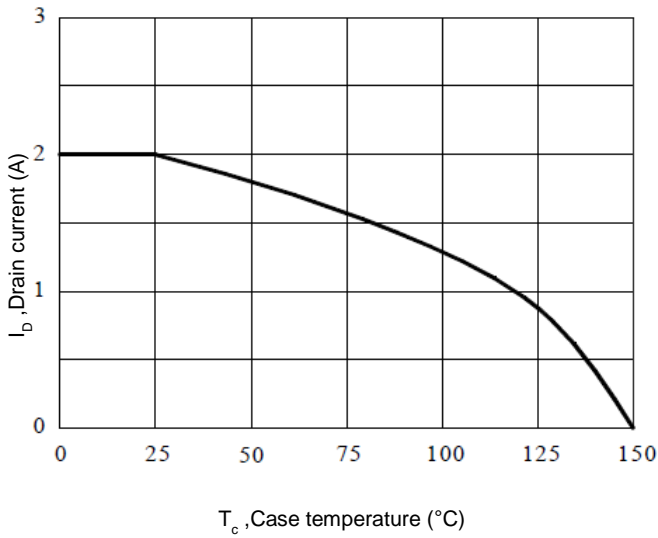


Figure 14. Body Diode Transfer Characteristics

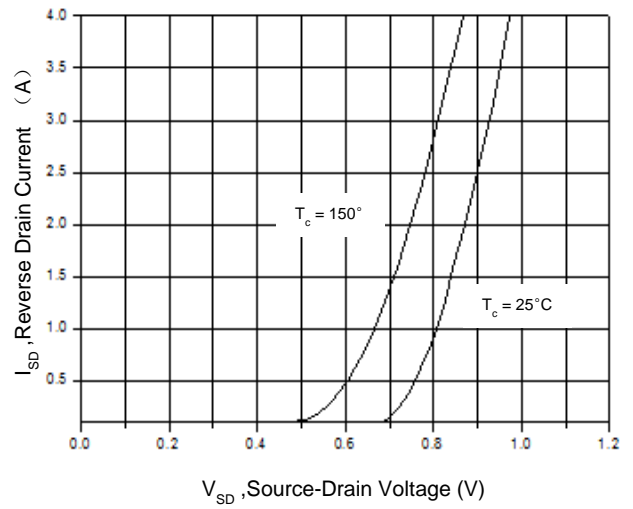


Figure 15 Transient Thermal Impedance, Junction to Case, TO-220F

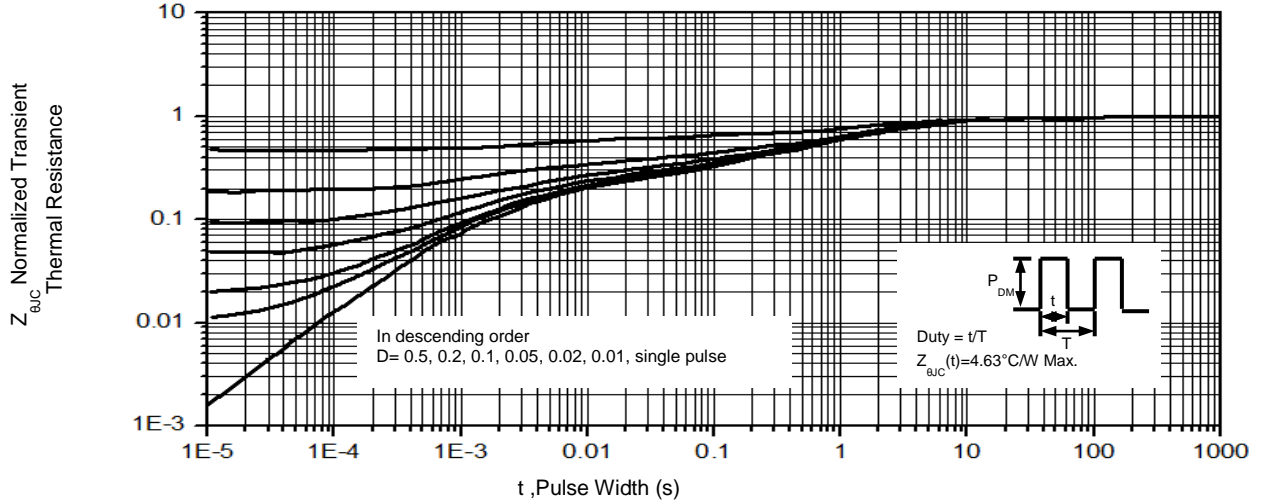
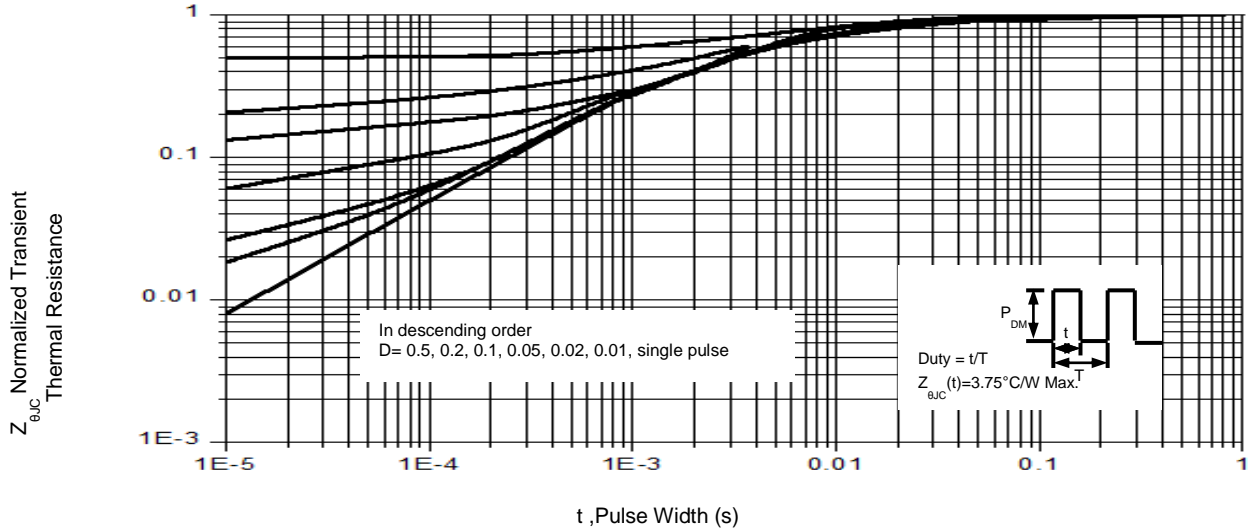
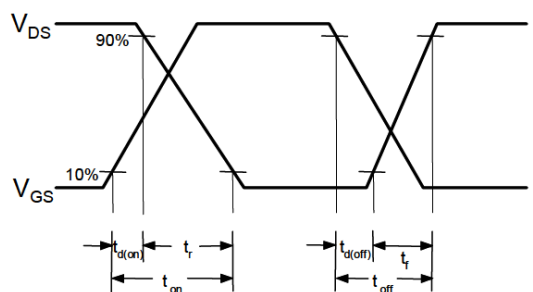
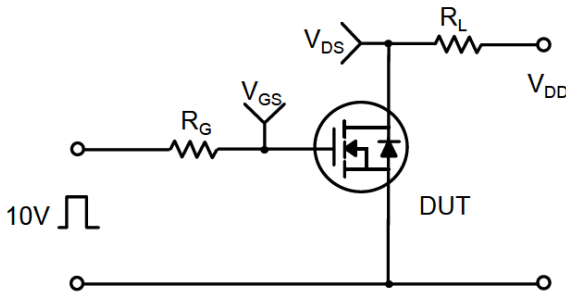


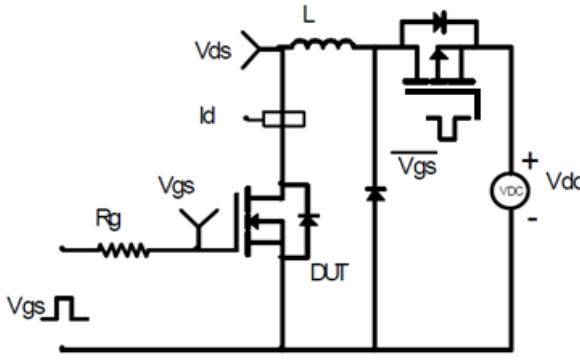
Figure 16. Transient Thermal Impedance, Junction to Case, TO-220/ TO-251/TO-252



**Gate Charge Test Circuit & Waveform**



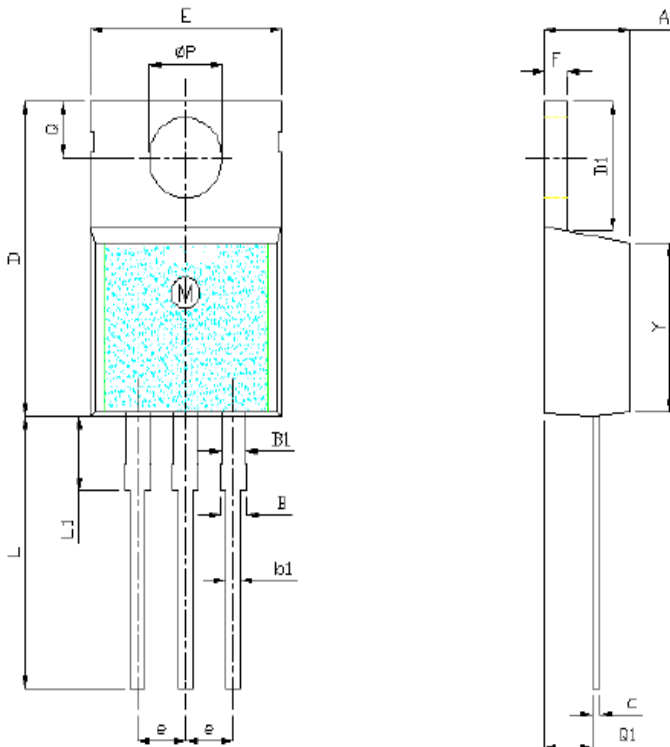
**Unclamped Inductive Switching Test Circuit & Waveforms**



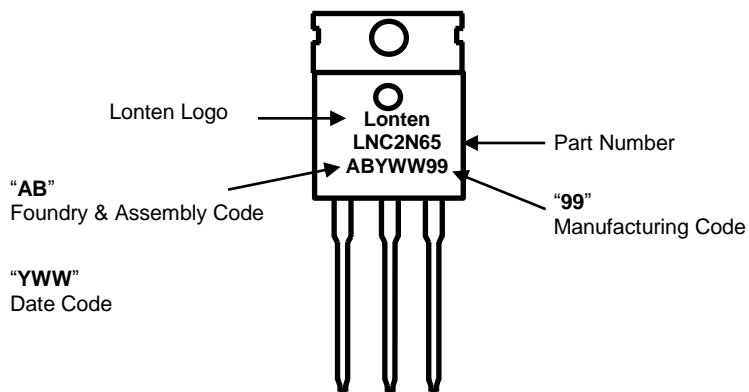
**Mechanical Dimensions for TO-220**

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	4		4.8	e	2.44	2.54	2.64
B	1.2		1.4	F	1.1		1.4
B1	1		1.4	L	12.5		14.5
b1	0.75		0.95	L1	3	3.5	4
c	0.4		0.55	ΦP	3.7	3.8	3.9
D	15		16.5	Q	2.5		3
D1	5.9		6.9	Q1	2		2.9
E	9.9		10.7	Y	8.02	8.12	8.22



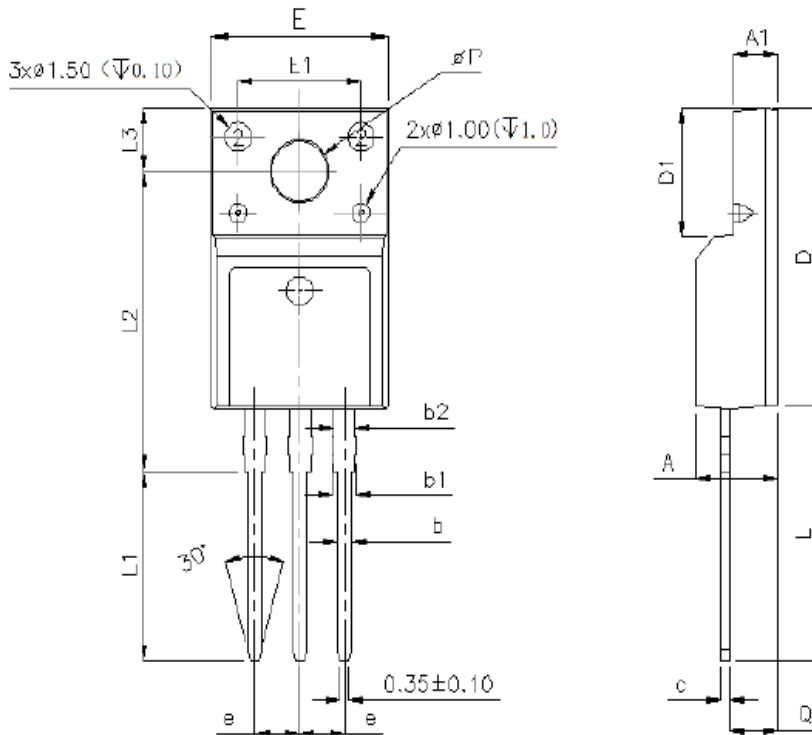
**TO-220 Part Marking Information**



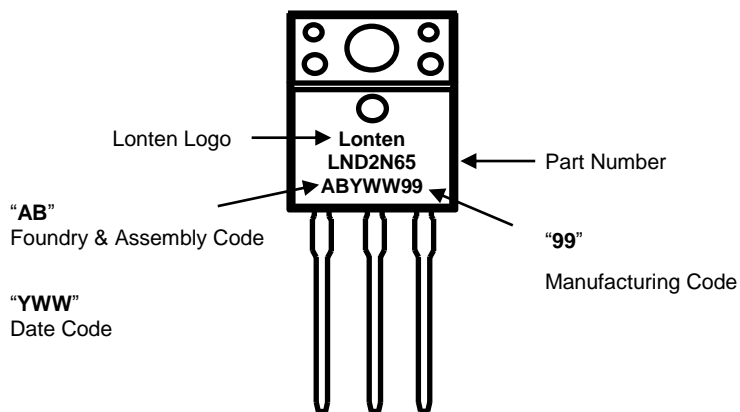
**Mechanical Dimensions for TO-220F**

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	4.5		4.9	E1	6.5	7	7.5
A1	2.3		2.9	e	2.44	2.54	2.64
b	0.65		0.9	L	12.5		14.3
b1	1.1		1.7	L1	9.45		10.05
b2	1.2		1.4	L2	15		16
c	0.35		0.65	L3	3.2		4.4
D	14.5		16.5	ΦP	3		3.3
D1	6.1		6.9	ø	2.5		2.9
E	9.6		10.3				



**TO-220F Part Marking Information**

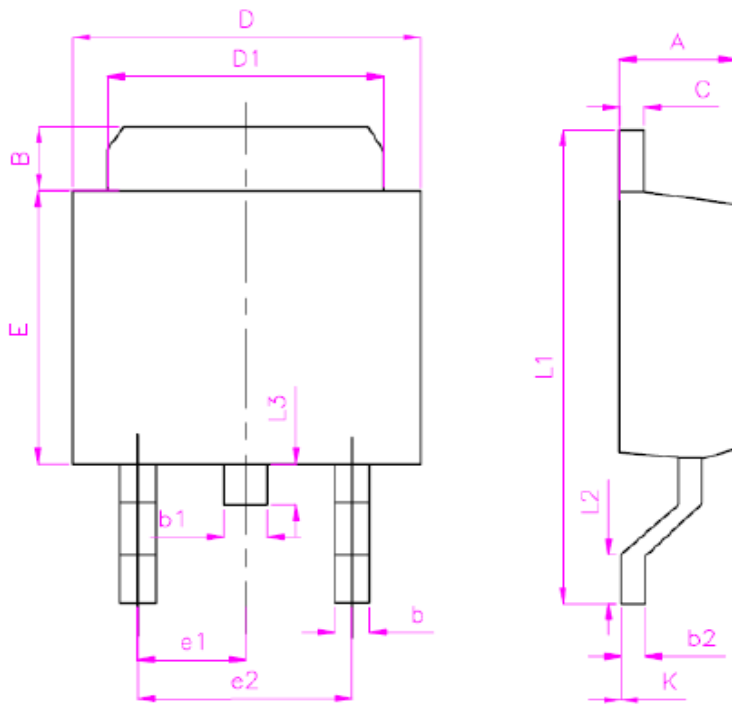




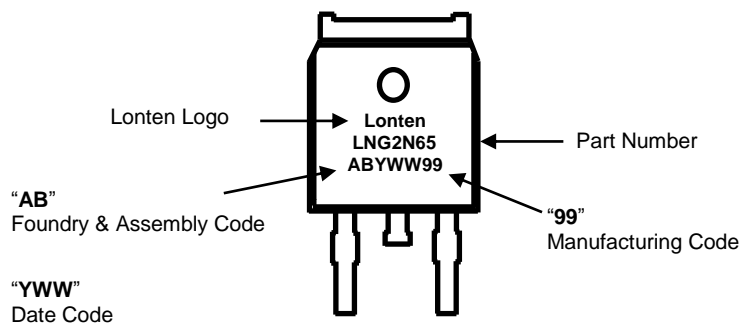
**Mechanical Dimensions for TO-252**

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	2.10		2.50	E	5.80		6.30
B	0.80		1.25	e1	2.25	2.30	2.35
b	0.50		0.85	e2	4.45		4.75
b1	0.50		0.90	L1	9.50		10.20
b2	0.45		0.60	L2	0.90		1.45
C	0.45		0.60	L3	0.60		1.10
D	6.35		6.75	K	-0.1		0.10
D1	5.10		5.50				



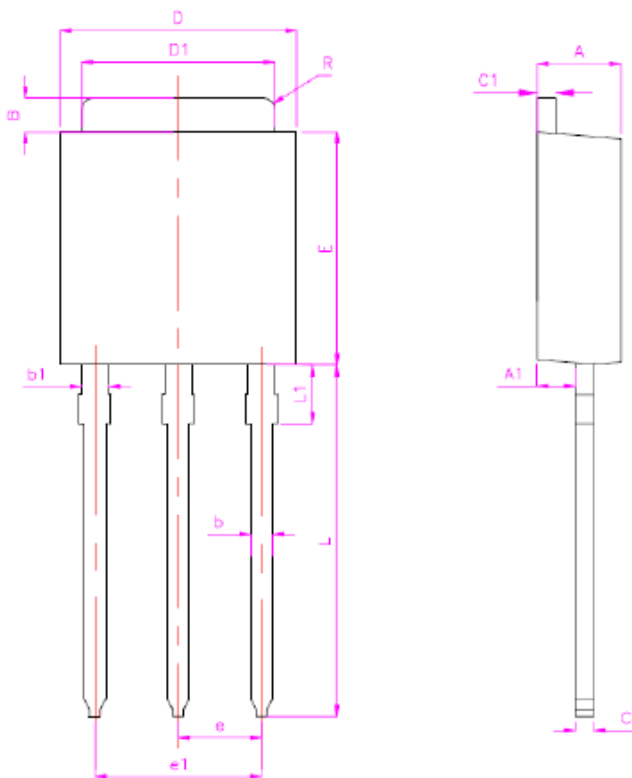
**TO-252 Part Marking Information**



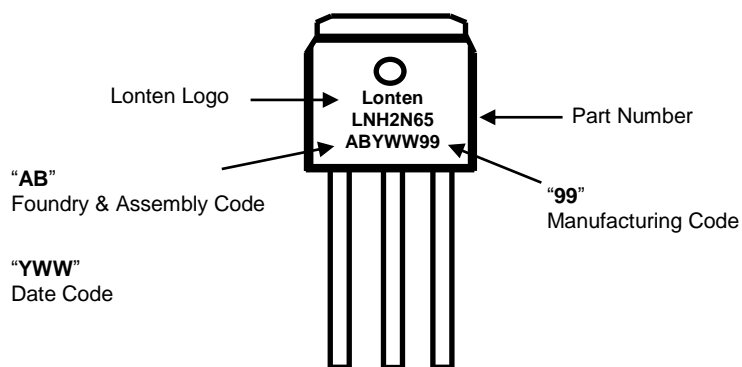
**Mechanical Dimensions for TO-251**

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	2.10		2.50	D1	5.10		5.50
A1	0.95		1.30	E	5.80		6.30
B	0.80		1.25	e	2.25	2.30	2.35
b	0.50		0.80	L	7.70		8.50
b1	0.70		0.90	L1	1.45		1.95
C	0.45		0.60	R		0.30	
C1	0.45		0.60				
D	6.35		6.75				



**TO-251 Part Marking Information**



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Jun. 2018 Revision 1.1

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